AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph **[0010]** with the following amended paragraph:

[0010] The p-type nitride semiconductor layer 500 is doped with an impurity such as Mg, and has a p-type conductivity through an activation process. U.S. Patent No.5,247,533 discloses a technology in which a p-type nitride semiconductor layer is activated by means of irradiation of electron beam. U.S. Patent No.5,306,662 discloses a technology in which a p-type nitride semiconductor layer is activated through annealing at a temperature of 400°C or more. Korean Patent No.~~10-043346~~ 10-0432246 discloses a technology in which NH3 and a hydrazine-based source material are used together as a nitrogen precursor for growing a p-type nitride semiconductor layer, so that the p-type nitride semiconductor layer has a p-type conductivity without an activation process.

Please replace paragraph **[0014]** with the following amended paragraph:

[0014] A variety of methods have been proposed in order to reduce the contact resistance between the p-type GaN used as the p-type nitride semiconductor layer 500 and the p-side electrode 600. Among them, there is a method in which the p-type nitride semiconductor layer 500 is not made of a single p-type GaN layer, but is formed to have a superlattice structure of p-type GaN/p-type InGaN or p-type GaN/p-type AlGaN, and the concentration of holes, which is significantly higher than the concentration that can be obtained in the single p-type GaN layer, is thus obtained within the superlattice structure through piezoelectric field. This method, however, is not preferred [[that]] because potential barrier is formed in a vertical direction within the superlattice structure before holes are injected into the active layer.

Please replace paragraph **[0015]**with the following amended paragraph:

[0015] As another example, there is a method in which a GaAs layer or an AlGaAs layer is grown, which can be doped with a high concentration (>1020 atoms/cm3), between the p-type nitride semiconductor layer 500 and the p-side electrode 600 (U.S. Patent No.6,410,944). In this method, however, since the bandgap of the GaAs layer or the AlGaAs layer is smaller than that of the visible region, most ~~. Most~~ of light generated from the active layer 400 may be absorbed by the GaAs layer or the AlGaAs layer. Therefore, this method has limited application fields.

Please replace paragraph **[0046]** with the following amended paragraph:

[0046] Table 1 shows electrical characteristics of a device, which is formed by growing silicon carbide of about 20Å in thickness, which is doped with a high concentration, on a common GaN-based light emitting device. At this time, an electrode used was an ITO(Indium Tin Oxide) electrode. From Table 1, it can be seen that a case where a silicon carbide layer is formed has a low contact resistance value compared to a case where an electrode is formed on p-type GaN without silicon carbide layer.